

MOS FIELD EFFECT TRANSISTOR

μ PA2810

SWITCHING

P-CHANNEL POWER MOSFET

DESCRIPTION

The μ PA2810 is P-channel MOSFET designed for DC/DC converter and power management applications of portable equipments.

FEATURES

- Low on-state resistance
 $R_{DS(on)1} = 12 \text{ m}\Omega \text{ MAX. (} V_{GS} = -10 \text{ V, } I_D = -13 \text{ A)}$
 $R_{DS(on)2} = 23 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.5 \text{ V, } I_D = -6.5 \text{ A)}$
- Built-in gate protection diode
- Thin type surface mount package with heat spreader
- RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, All terminals are connected.)

Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	-30	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC)	I _{D(DC)}	±13	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	±78	A
Total Power Dissipation ^{Note2}	P _{T1}	1.5	W
Total Power Dissipation (PW = 10 sec) ^{Note2}	P _{T2}	3.8	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current ^{Note3}	I _{AS}	-13	A
Single Avalanche Energy ^{Note3}	E _{AS}	16.9	mJ

THERMAL RESISTANCE

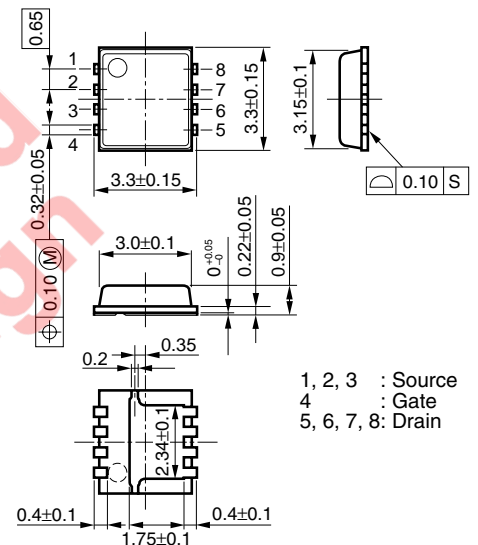
Channel to Ambient Thermal Resistance ^{Note2}	R _{th(ch-A)}	83.3	°C/W
Channel to Case (Drain) Thermal Resistance	R _{th(ch-C)}	2.4	°C/W

- Notes 1.** PW ≤ 10 μs, Duty Cycle ≤ 1%
- 2.** Mounted on FR-4 board of 25.4 mm x 25.4 mm x 0.8 mm
- 3.** Starting T_{ch} = 25°C, V_{DD} = -15 V, R_G = 25 Ω, V_{GS} = -20 → 0 V, L = 100 μH

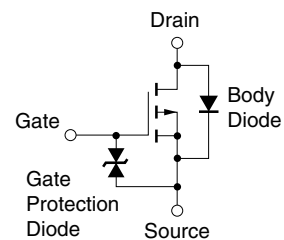
Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT

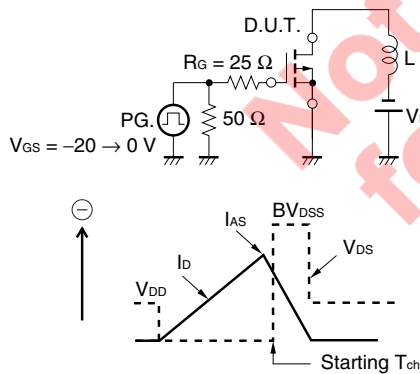


ELECTRICAL CHARACTERISTICS (TA = 25°C, All terminals are connected.)

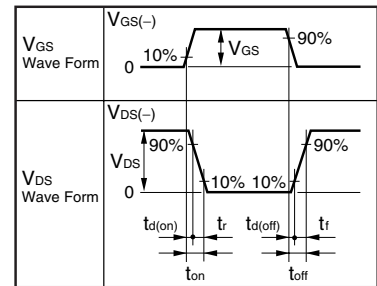
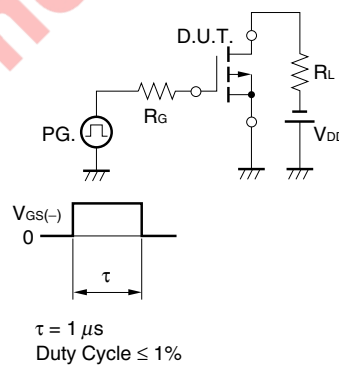
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			±10	μA
Gate to Source Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$	-1.0		-2.5	V
Forward Transfer Admittance ^{Note}	$ y_{fs} $	$V_{DS} = -10\text{ V}, I_D = -6.5\text{ A}$	7			S
Drain to Source On-state Resistance ^{Note}	$R_{DS(on)1}$	$V_{GS} = -10\text{ V}, I_D = -13\text{ A}$		9.5	12	mΩ
	$R_{DS(on)2}$	$V_{GS} = -4.5\text{ V}, I_D = -6.5\text{ A}$		15	23	mΩ
Input Capacitance	C_{iss}	$V_{DS} = -10\text{ V},$		1860		pF
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V},$		400		pF
Reverse Transfer Capacitance	C_{rss}	$f = 1\text{ MHz}$		300		pF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, I_D = -6.5\text{ A},$		11		ns
Rise Time	t_r	$V_{GS} = -10\text{ V},$		19		ns
Turn-off Delay Time	$t_{d(off)}$	$R_G = 10\ \Omega$		160		ns
Fall Time	t_f			100		ns
Total Gate Charge	Q_G	$V_{DD} = -24\text{ V},$		40		nC
Gate to Source Charge	Q_{GS}	$V_{GS} = -10\text{ V},$		6		nC
Gate to Drain Charge	Q_{GD}	$I_D = -13\text{ A}$		14		nC
Body Diode Forward Voltage ^{Note}	$V_{F(S-D)}$	$I_F = 13\text{ A}, V_{GS} = 0\text{ V}$		0.87		V
Reverse Recovery Time	t_{rr}	$I_F = 13\text{ A}, V_{GS} = 0\text{ V},$		50		ns
Reverse Recovery Charge	Q_{rr}	$di/dt = 100\text{ A}/\mu\text{s}$		40		nC

Note Pulsed

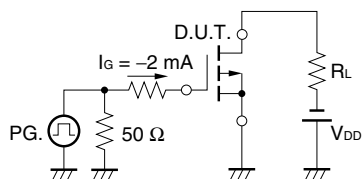
TEST CIRCUIT 1 AVALANCHE CAPABILITY



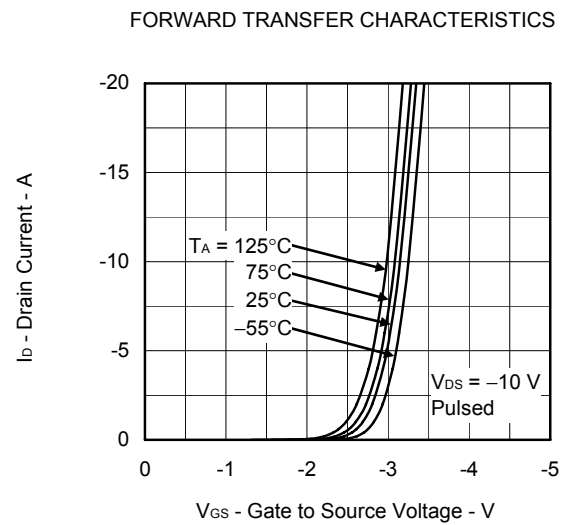
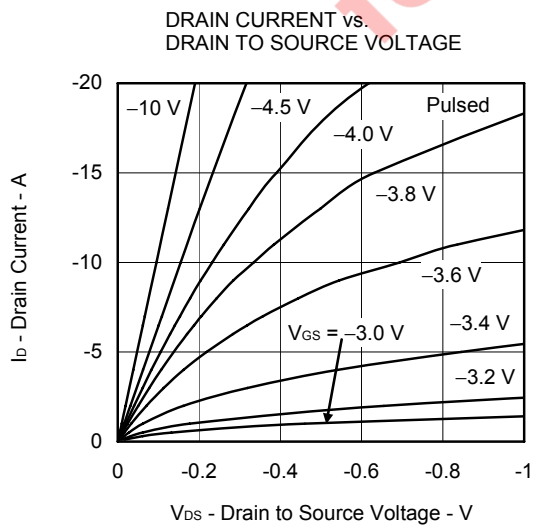
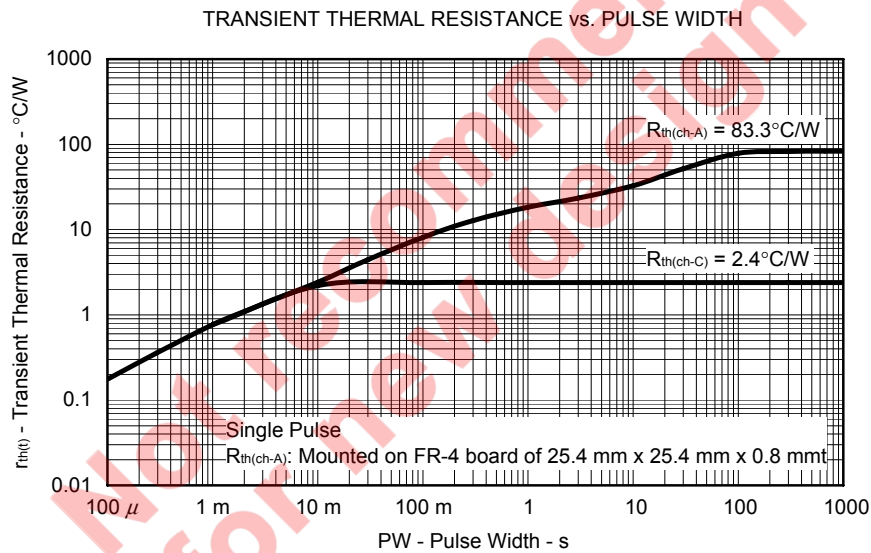
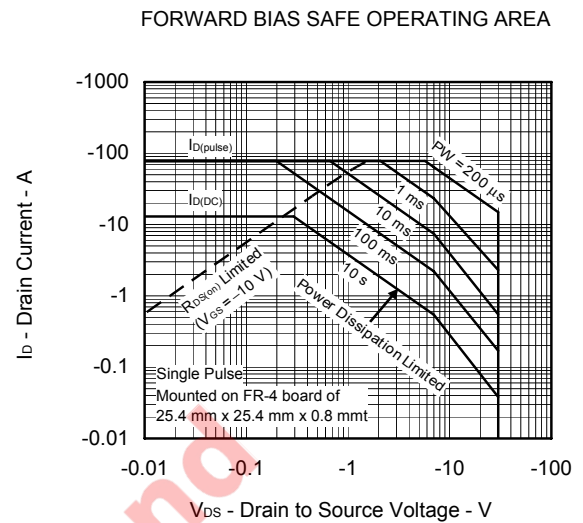
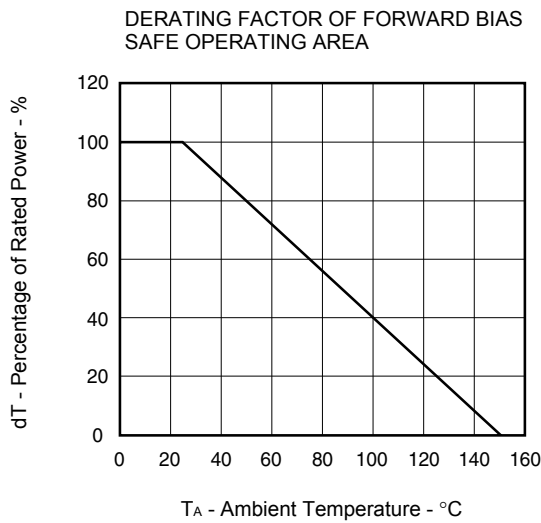
TEST CIRCUIT 2 SWITCHING TIME

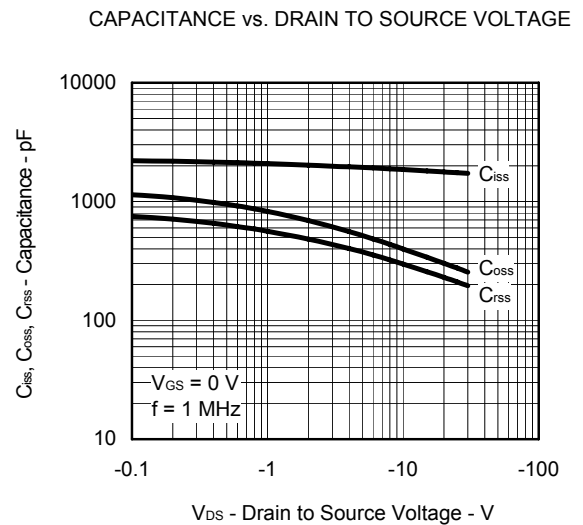
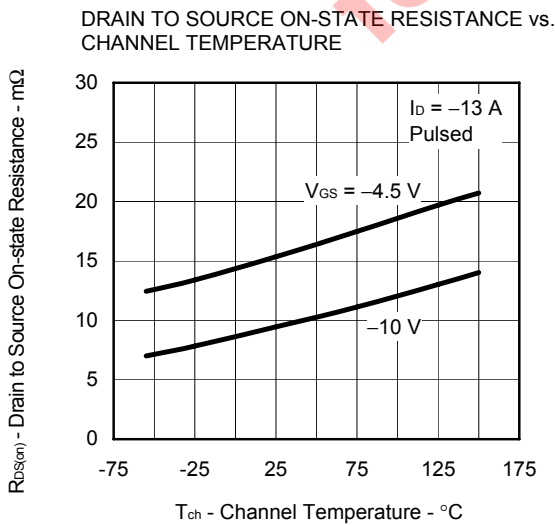
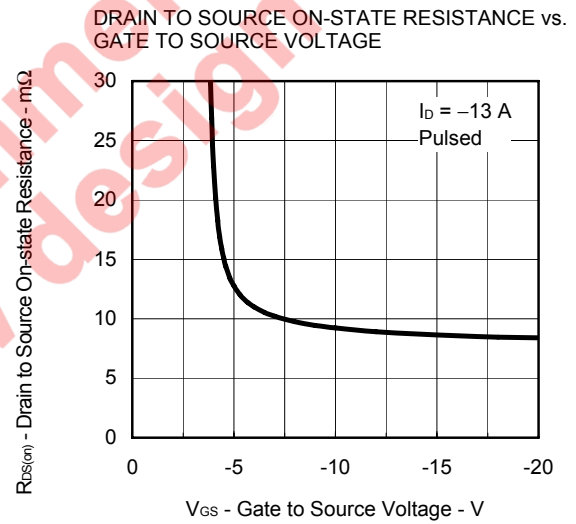
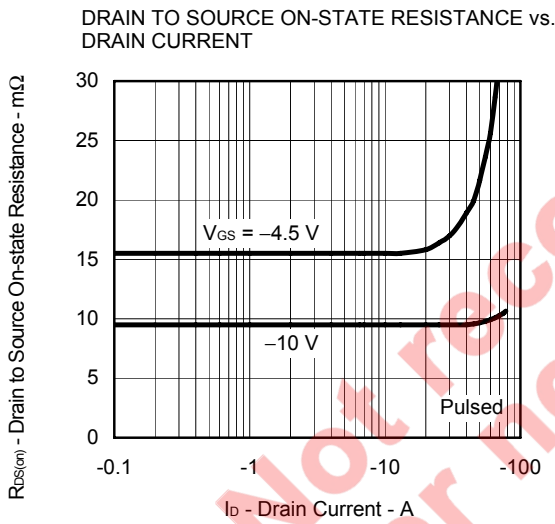
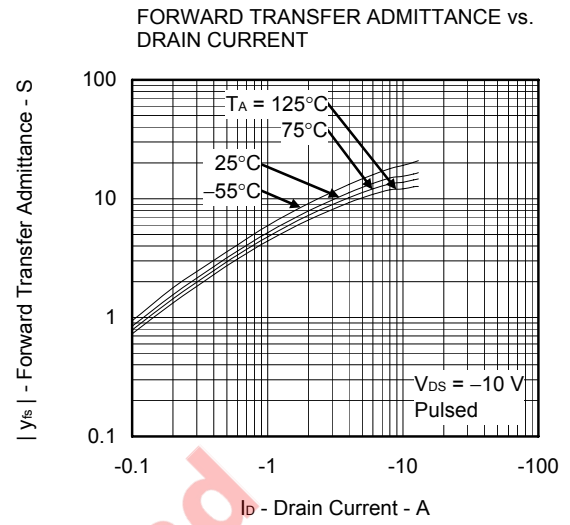
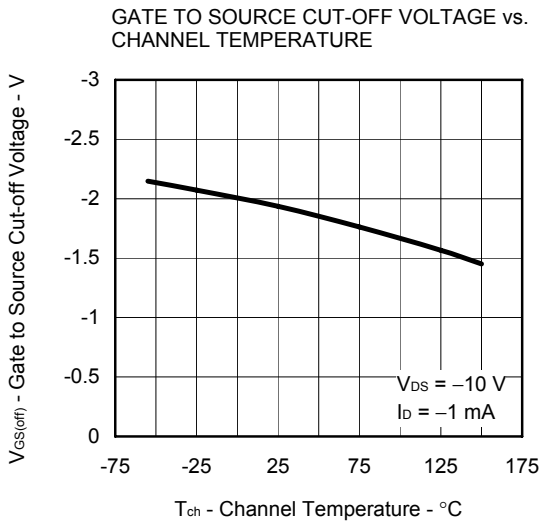


TEST CIRCUIT 3 GATE CHARGE

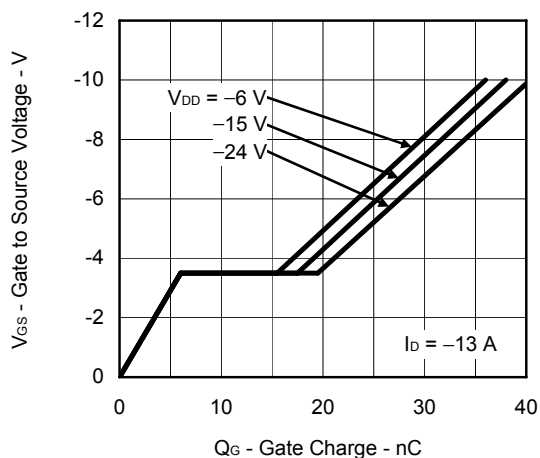


TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

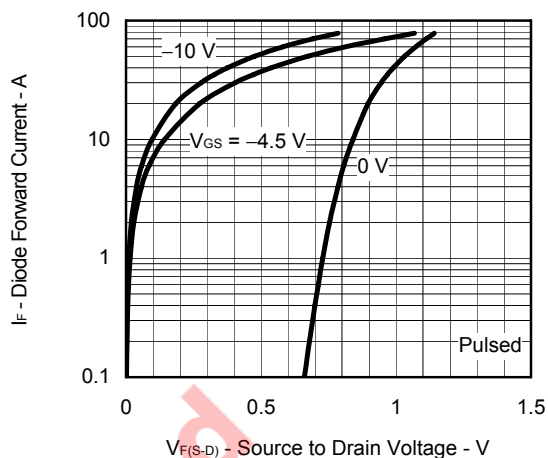




DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
μPA2810T1L-E1-AY <small>Note</small>	Pure Sn	Tape 3000 p/reel	8-pin HVSON (3333) 0.028 g TYP.
μPA2810T1L-E2-AY <small>Note</small>			

Note Pb-free (This product does not contain Pb in the external electrode.)

Not recommended for new design